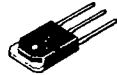


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2SD1400



2022

NPN Triple Diffused Planar Silicon Transistor

Color TV Horizontal Deflection Output Applications

©1267B

Features:

- High breakdown voltage and high reliability
- High switching speed
- Capable of being mounted easily due to one-point fixing type plastic mold package

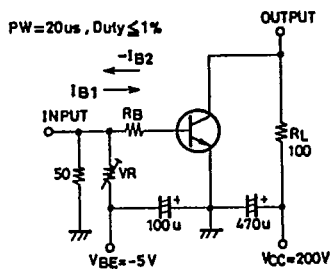
Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	V _{CBO}	1500	V
Collector to Emitter Voltage	V _{CEO}	800	V
Emitter to Base Voltage	V _{EBO}	7	V
Collector Current	I _C	2.5	A
Peak Collector Current	i _{cp}	10	A
Collector Dissipation	P _C	80	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

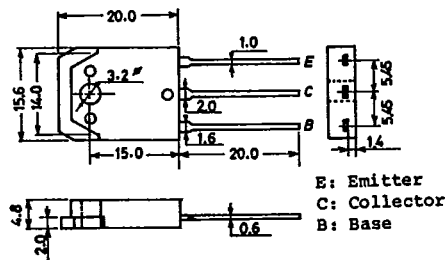
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I _{CBO}	V _{CB} =800V, I _E =0			10	uA
Emitter Cutoff Current	I _{EBO}	V _{EB} =5V, I _C =0			1	mA
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =0.5A	8			
Gain Bandwidth Product	f _T	V _{CE} =10V, I _C =0.5A		3		MHz
C-E Saturation Voltage	V _{CE(sat)}	I _C =2A, I _B =0.6A			8	V
B-E Saturation Voltage	V _{BE(sat)}	I _C =2A, I _B =0.6A			1.5	V
C-B Breakdown Voltage	V(BR) _{CBO}	I _C =5mA, I _E =0	1500			V
C-E Breakdown Voltage	V(BR) _{CEO}	I _C =100mA, R _{BE} =∞	800			V
E-B Breakdown Voltage	V(BR) _{EBO}	I _E =200mA, I _C =0	7			V
Fall Time	t _f	I _C =2A, I _{B1} =0, 6A, I _{B2} =-1.2A			0.4	us

Switching Time Test Circuit

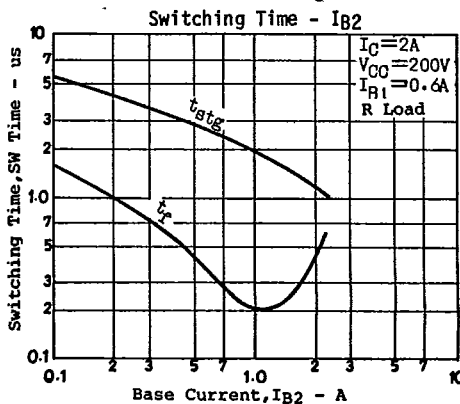
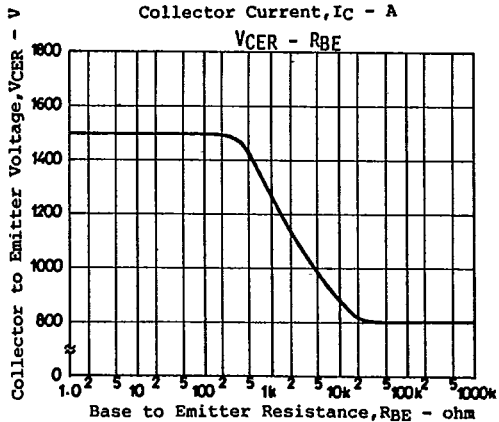
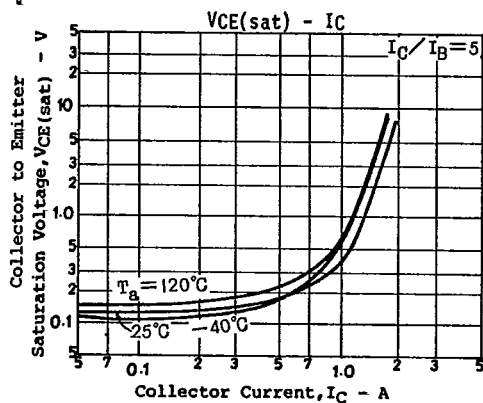
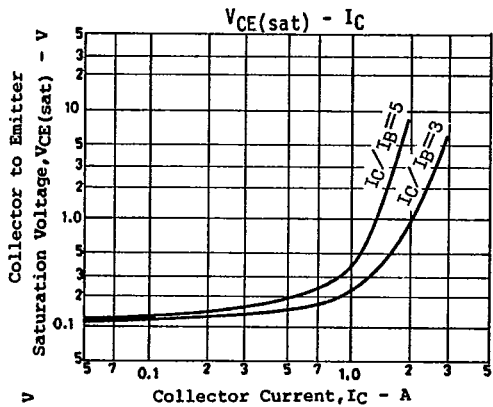
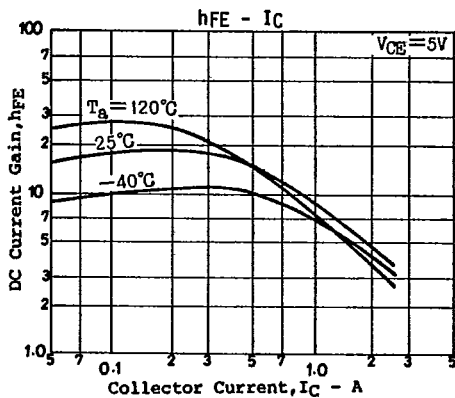
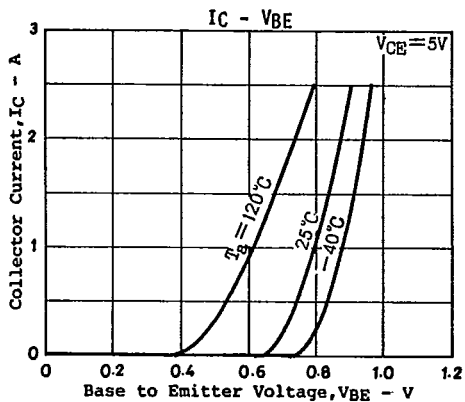
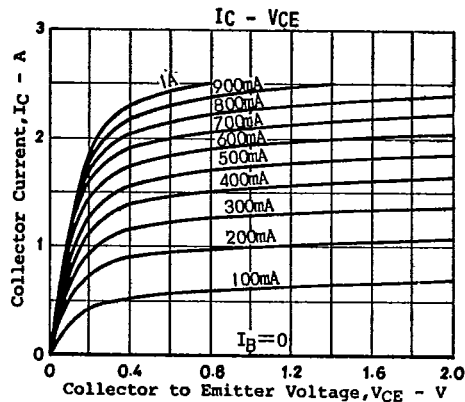
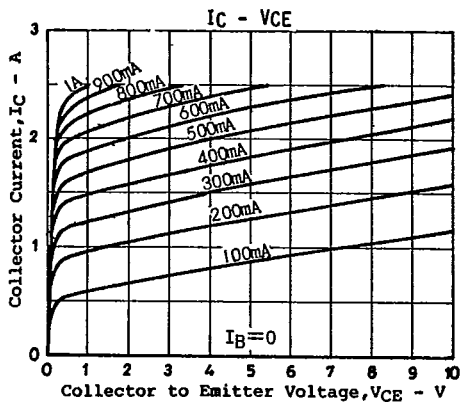


Case Outline 2022 (unit:mm)



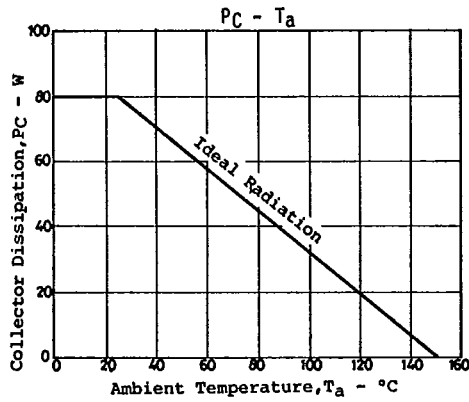
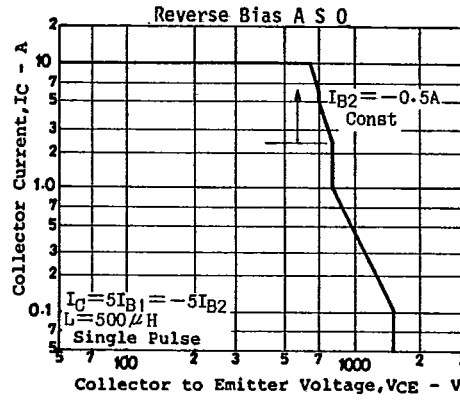
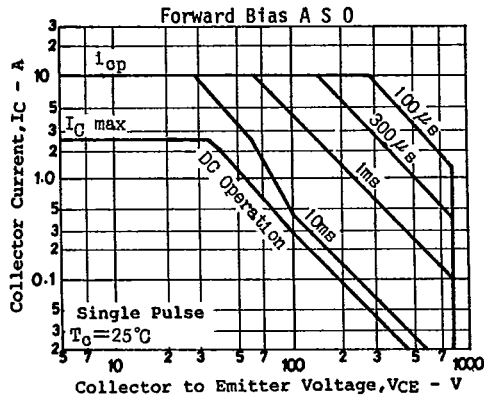
2SD1400

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2SD1400

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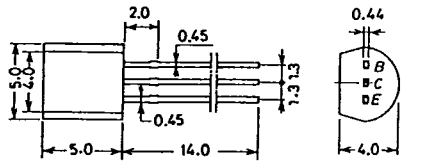
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CASE OUTLINES AND ATTACHMENTS

- All of Sanyo Transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.

Case Outline-[2003A]

unit:mm

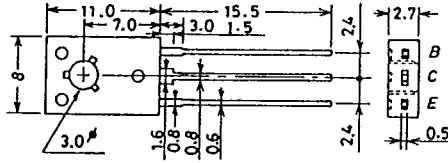


JEDEC: TO-92
EIAJ: SC-43
SANYO: NP

B. Base
C. Collector
E. Emitter

Case Outline-[2009A]

unit:mm

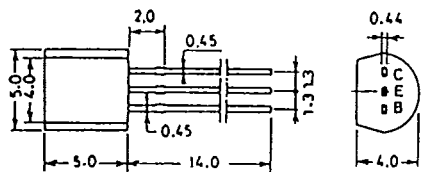


JEDEC: TO-126

B: Base
C: Collector
E: Emitter

Case Outline-[2004A]

unit:mm

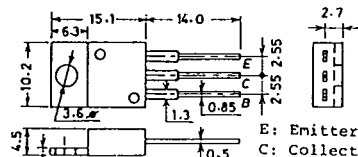


JEDEC: TO-92
EIAJ: SC-43
SANYO: NP

C. Collector
E. Emitter
B. Base

Case Outline-[2010A]

unit:mm

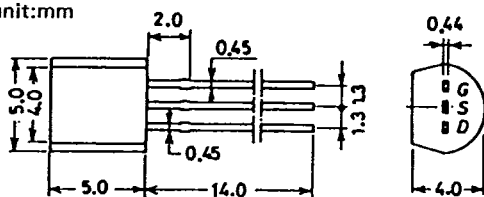


JEDEC: TO-220AB
EIAJ: SC-46

E: Emitter
C: Collector
B: Base

Case Outline-[2005A]

unit:mm

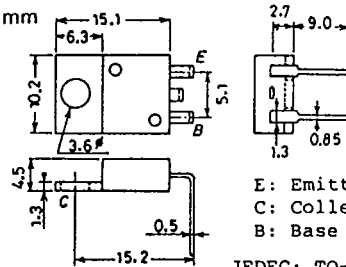


JEDEC: TO-92
EIAJ: SC-43
SANYO: NP

G: Gate
S: Source
D: Drain
B: Base
C: Collector

Case Outline-[2012]

unit:mm

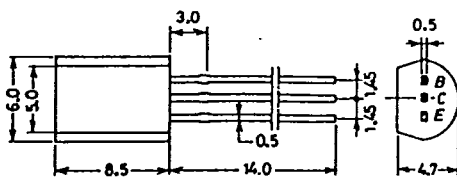


JEDEC: TO-220AA
EIAJ: SC-45

E: Emitter
C: Collector
B: Base

Case Outline-[2006A]

unit:mm

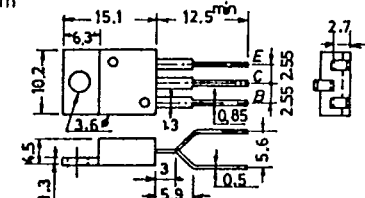


EIAJ: SC-51
SANYO: MP

B: Base
C: Collector
E: Emitter

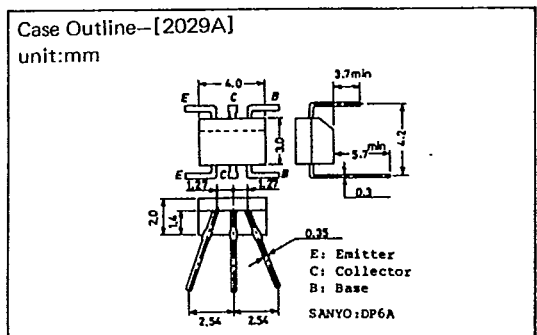
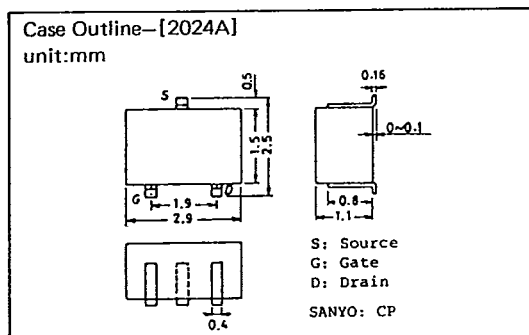
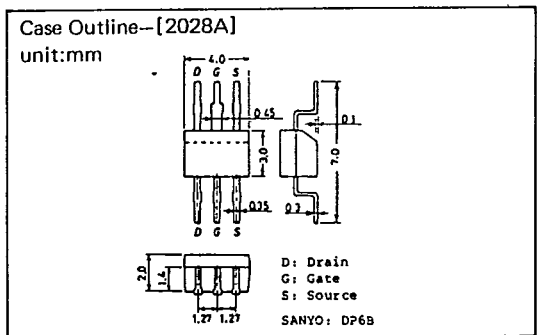
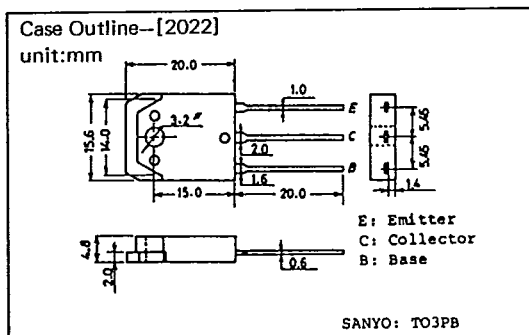
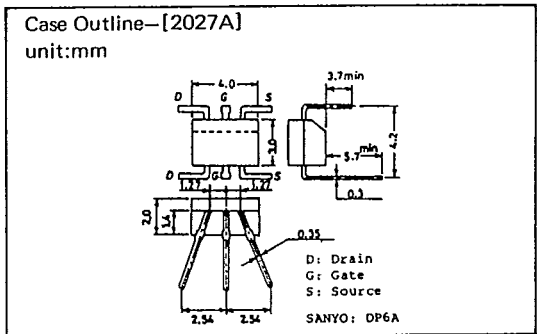
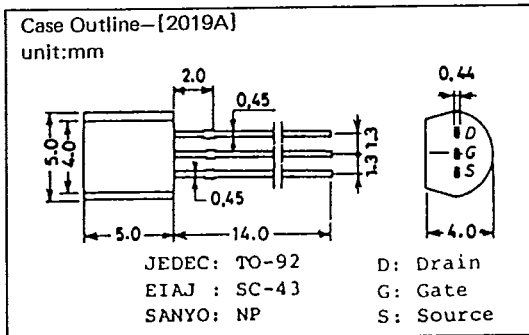
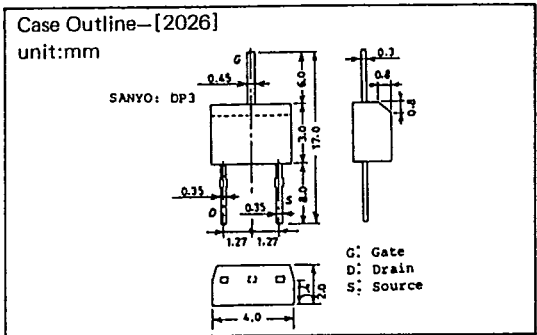
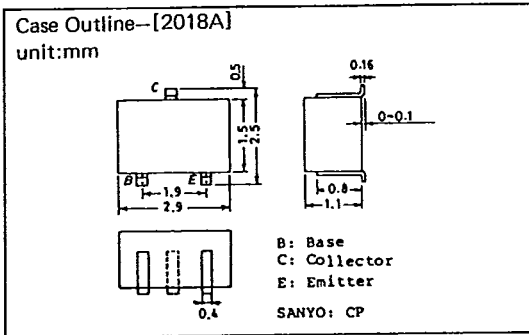
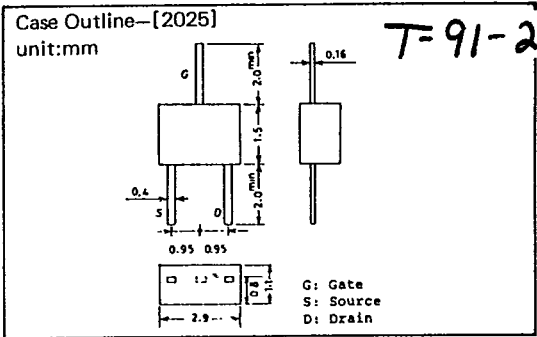
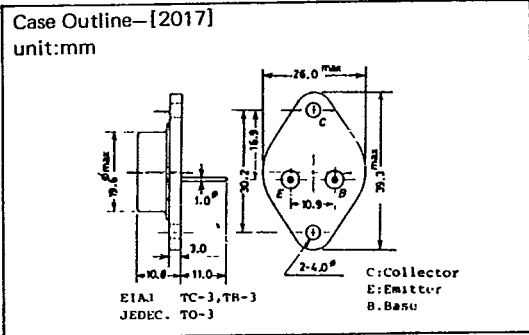
Case Outline-[2013]

unit:mm

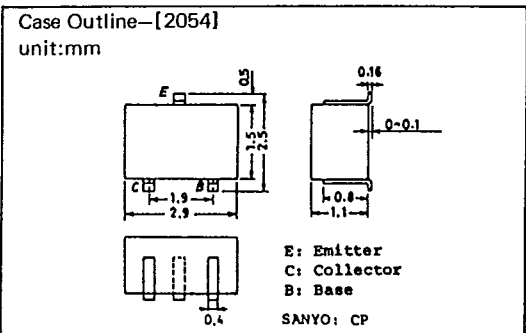
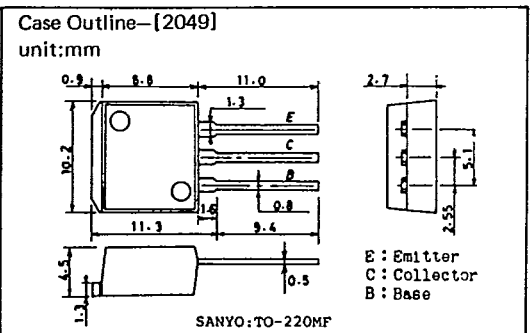
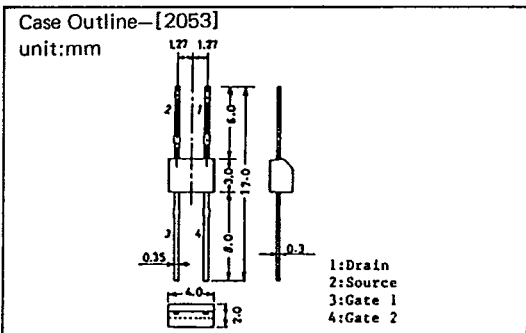
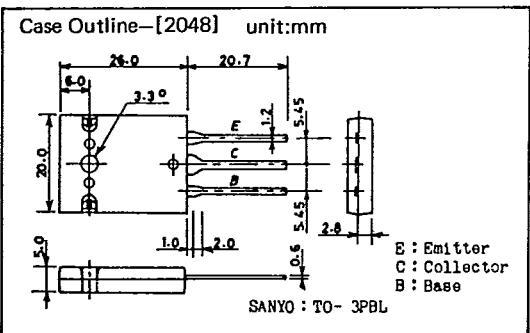
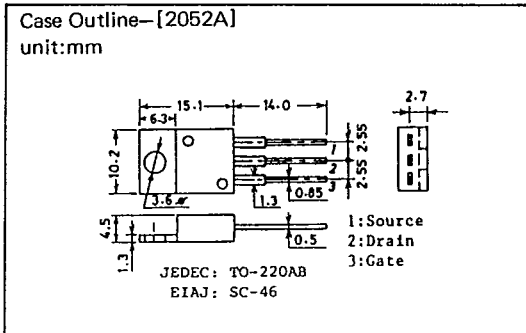
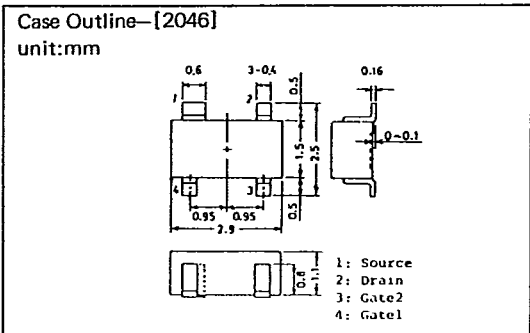
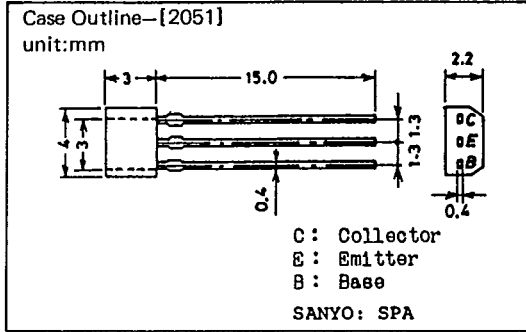
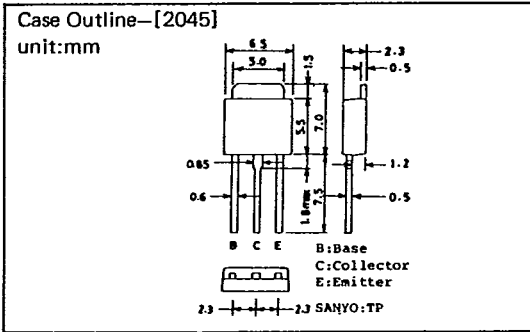
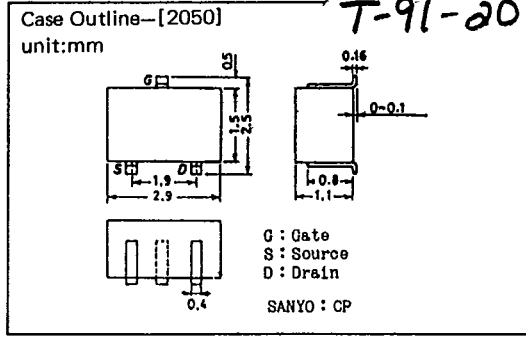
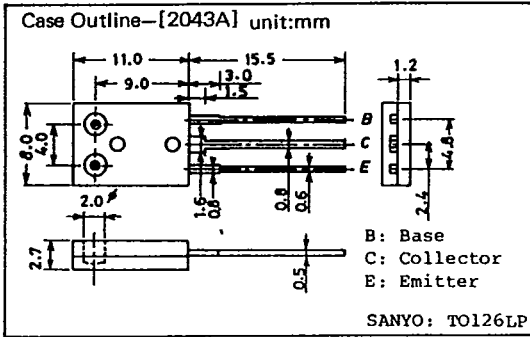


JEDEC TO-220

B: Base
C: Collector
E: Emitter



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T-91-20

